

HEXFET® Power MOSFETs

International
IOR Rectifier

Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_D Continuous Drain Current 70°C (A)	$R_{\theta A}$ Max Thermal Resistance (°C/W)	P_D Max. Power Dissipation @ $T_A = 25^\circ\text{C}$ (W)	Fax-on- Demand
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Surface Mount

Micro3™ (SOT-23)

N-Channel	<i>Logic Level</i>						
IRLML2402*	20	0.25	0.93	0.74	370	340	91257
IRLML2803	30	0.25	0.91	0.73	370	340	91258
P-Channel	<i>Logic Level</i>						
IRLML5103	-30	0.6	-0.6	-0.48	370	280	91260
IRLML6302*	-20	0.6	-0.61	-0.49	370	280	91259

* Indicates low $V_{GS(th)}$, which can operate at $V_{GS} = 2.75V$

HEXFET® Power MOSFETs

International
 Rectifier

Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_D Continuous Drain Current 100°C (A)	$R_{\theta C}$ Max Thermal Resistance (°C/W)	P_D Max. Power Dissipation @ $T_C = 25^\circ\text{C}$ (W)	Fax-on- Demand
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Surface Mount

Micro6™

N-Channel	<i>Logic Level</i>						
IRLMS1503	30	0.1	2.2	1.8	160	780	91508
IRLMS1902*	20	0.1	2.2	1.8	160	780	91540
P-Channel	<i>Logic Level</i>						
IRLMS5703	-30	0.2	-1.6	-1.3	75	780	91413
IRLMS6702*	-20	0.2	-1.6	-1.3	160	780	91414

* Indicates low $V_{GS(th)}$, which can operate at $V_{GS} = 2.75V$

HEXFET® Power MOSFETs

Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_D Continuous Drain Current 70°C (A)	$R_{\theta A}$ Max Thermal Resistance (°C/W)	P_D Max. Power Dissipation @ $T_A = 25^\circ\text{C}$ (W)	Fax-on- Demand
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Surface Mount

Micro8™

N-Channel	<i>Logic Level</i>						
IRF7601*	20	0.035	3.8	3	160	780	91261
IRF7603	30	0.035	3.7	3	160	780	91262
Dual N-Channel	<i>Logic Level</i>						
IRF7501*	20	0.135	1.7	1.4	200	625	91265
IRF7503	30	0.135	1.7	1.4	200	625	91266
P-Channel	<i>Logic Level</i>						
IRF7604*	-20	0.09	-2.4	-1.9	160	780	91263
IRF7606	-30	0.09	-2.4	-1.9	160	780	91264
Dual P-Channel	<i>Logic Level</i>						
IRF7504*	-20	0.27	-1.2	-0.96	200	625	91267
IRF7506	-30	0.27	-1.2	-0.96	200	625	91268
Dual N- and P-Channel	<i>Logic Level</i>						
IRF7507*	20	0.135	1.7	1.3	200	625	91269
	-20	0.27	-1.2	-0.96	200	625	91269
IRF7509	30	0.135	1.7	1.3	200	625	91270
	-30	0.27	-1.2	-0.96	200	625	91270

* Indicates low $V_{GS(th)}$, which can operate at $V_{GS} = 2.75V$

HEXFET® Power MOSFETs

Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_D Continuous Drain Current 70°C (A)	$R_{\theta A}$ Max Thermal Resistance (°C/W)	P_D Max. Power Dissipation @ $T_A = 25^\circ\text{C}$ (W)	Fax-on- Demand
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Surface Mount

SO-8

N-Channel

IRF7413	30	0.011	10	5.8	62.5	2	91330
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N-Channel

Logic Level

IRF7201	30	0.03	7	5.6	80	1.6	91100
IRF7401	20	0.022	6.9	5.5	80	1.6	91244
IRF7403	30	0.022	6.7	5.4	80	1.6	91245

Dual N-Channel

Logic Level

IRF7101	20	0.1	3.5	2.3	90	1.4	90871
IRF7103	50	0.13	3	2.3	90	1.4	91095
IRF7301	20	0.05	4.3	3.4	90	1.4	91238
IRF7303	30	0.05	4	3.2	90	1.4	91239
IRF7311	20	0.026	5.9	4.1	0.026	1.4	91435
IRF7313	30	0.029	6.5	5.2	62.5	2	91480
IRF9956	30	0.1	3.5	2.8	62.5	2	91559

P-Channel

Logic Level

IRF7204	-20	0.06	-5.3	-4.2	80	1.6	91103
IRF7205	-30	0.07	-4.6	-3.7	80	1.6	91104
IRF7404	-20	0.04	-5.3	-4.3	80	1.6	91246
IRF7406	-30	0.045	-4.7	-3.8	80	1.6	91247
IRF7416	-30	0.02	-8.8	-5.6	50	1	91356

HEXFET® Power MOSFETs

International
IR Rectifier

Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_D Continuous Drain Current 70°C (A)	$R_{\theta A}$ Max Thermal Resistance (°C/W)	P_D Max. Power Dissipation @ $T_A = 25^\circ\text{C}$ (W)	Fax-on- Demand
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Surface Mount

SO-8

Dual P-Channel	<i>Logic Level</i>						
IRF7104	-20	0.25	-2.3	-1.8	90	1.4	91096
IRF7304	-20	0.09	-3.6	-2.9	90	1.4	91240
IRF7306	-30	0.1	-3	-2.4	90	1.4	91241
IRF7314	-20	0.053	-4.2	-2.9	190	1.4	91435
IRF7316	-30	0.058	-4.9	-3.9	62.5	2	91505
IRF9953	-30	0.25	-2.3	-1.8	62.5	2	91560
Dual N- and P-Channel	<i>Logic Level</i>						
IRF7105	25	0.1	3.5	2.8	90	1.4	91097
	-20	0.27	-1.2	-0.96	200	625	91097
IRF7307	20	0.05	4.3	3.4	90	1.4	91242
	-20	0.09	-4	-2.9	90	1.4	91242
IRF7309	30	0.05	4	3.2	90	1.4	91243
	-30	0.1	-3.5	-2.4	90	1.4	91243
IRF9952	30	0.1	3.5	2.8	62.5	2	91562
	-30	0.25	-2.3	-1.8	62.5	2	91562

HEXFET® Power MOSFETs

International
 Rectifier

Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_D Continuous Drain Current 100°C (A)	$R_{\theta C}$ Max Thermal Resistance (°C/W)	P_D Max. Power Dissipation @ $T_C = 25^\circ\text{C}$ (W)	VFM Forward Voltage Drop @ $T_j = 25^\circ\text{C}$	Fax-on- Demand
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Surface Mount

FETKY™ SO-8

N-Channel	<i>FETKY (Co-packaged HEXFET Power MOSFET and Schottky Diode)</i>							
IRF7421D1	30	0.035	4.1	3.3	50	2.5	0.50V @ 1.0A	91411
IRF7422D2	-20	0.09	-2.9	-2.3	50	2.5	0.57V @ 3.0A	91412

HEXFET® Power MOSFETs

Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_D Continuous Drain Current 100°C (A)	$R_{\theta A}$ Max Thermal Resistance (°C/W)	P_D Max. Power Dissipation @ $T_C = 25^\circ\text{C}$ (W)	Fax-on- Demand
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Surface Mount

SOT-223 (TO-261AA)

N-Channel

IRFL014	60	0.2	2.7	1.7	60	2	90860
IRFL110	100	0.54	1.5	0.96	60	2	90861
IRFL210	200	1.5	0.96	0.6	60	2	90868
IRFL214	250	2	0.79	0.5	60	2	90862
IRFL4105	55	0.045	3.7		60	2.1	91381
IRFL4310	100	0.2	1.6		60	2.1	91368

N-Channel

Logic Level

IRLL014N	55	0.14	2.8	1.6	60	2.1	91499
IRLL110	100	0.54	1.5	0.93	40	3.1	90869
IRLL2705	55	0.04	5.2	3	60	2.1	91380
IRLL3303	30	0.031	6.5	3.7	60	2.1	91379

P-Channel

IRFL9014	-60	0.5	-1.8	-1.1	60	2	90863
IRFL9110	-100	1.2	-1.1	-0.69	60	2	90864

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Surface Mount

TO-252AA (D-Pak)

N-Channel

IRFR014	60	0.2	7.7	4.9	5	25	90701
IRFR024N	55	0.075	16	10	3.3	38	91336
IRFR110	100	0.54	4.3	2.7	5	25	90524
IRFR1205	55	0.027	37	23	1.8	69	91318
IRFR120N	100	0.21	9.1	5.8	3.2	39	91365
IRFR210	200	1.5	2.6	1.7	5	25	90526
IRFR214	250	2	2.2	1.4	5	25	90703
IRFR220	200	0.8	4.8	3	3	42	90525
IRFR224	250	1.1	3.8	2.4	3	42	90600
IRFR310	400	3.6	1.7	1.1	5	25	90597
IRFR320	400	1.8	3.1	2	3	42	90598
IRFR3910	100	0.11	15	9.5	2.4	52	91364
IRFR4105	55	0.045	25	16	2.7	48	91302
IRFR420	500	3	2.4	1.5	3	42	90599
IRFRC20	600	4.4	2	1.3	3	42	90637

N-Channel

Logic Level

IRLR014	60	0.2	7.7	4.9	5	25	90624
IRLR024N	55	0.065	17	11	3.3	38	91363
IRLR110	100	0.54	4.3	2.7	5	25	90633
IRLR120	100	0.27	7.7	4.9	3	42	90636

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International
IR Rectifier

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Surface Mount

TO-252AA (D-Pak)

IRLR2703	30	0.045	22	14	3.3	38	91335
IRLR2905	55	0.027	36	23	1.8	69	91334
IRLR3103	30	0.019	46	29	1.8	69	91333
P-Channel							
IRFR9014	-60	0.5	-5.1	-3.2	5	25	90654
IRFR9024	-60	0.28	-8.8	-5.6	3	42	90655
IRFR9110	-100	1.2	-3.1	-2	5	25	90519
IRFR9120	-100	0.6	-5.6	-3.6	3	42	90520
IRFR9210	-200	3	-1.9	-1.2	5	25	90521
IRFR9220	-200	1.5	-3.6	-2.3	3	42	90522
P-Channel							
	<i>Logic Level</i>						
IRLR2705	55	0.04	24	15	2.7	46	91317

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Discrete

TO-251AA (I-Pak)

N-Channel

IRFU014	60	0.2	7.7	4.9	5	25	90701
IRFU024N	55	0.075	16	10	3.3	38	91336
IRFU110	100	0.54	4.3	2.7	5	25	90524
IRFU1205	55	0.027	37	23	1.8	69	91318
IRFU120N	100	0.21	9.1	5.8	3.2	39	91365
IRFU210	200	1.5	2.6	1.7	5	25	90526
IRFU214	250	2	2.2	1.4	5	25	90703
IRFU220	200	0.8	4.8	3	3	42	90525
IRFU224	250	1.1	3.8	2.4	3	42	90600
IRFU310	400	3.6	1.7	1.1	5	25	90597
IRFU320	400	1.8	3.1	2	3	42	90598
IRFU3910	100	0.11	15	9.5	2.4	52	91364
IRFU4105	55	0.045	25	19	2.7	48	91302
IRFU420	500	3	2.4	1.5	3	42	90599
IRFUC20	600	4.4	2	1.3	3	42	90637

N-Channel

Logic Level

IRLU014	60	0.2	7.7	4.9	5	25	90624
IRLU024N	55	0.065	17	11	3.3	38	91363
IRLU110	100	0.54	4.3	2.7	5	25	90633
IRLU120	100	0.27	7.7	4.9	3	42	90636

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 Rectifier

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Discrete

TO-251AA (I-Pak)

IRLU2703	30	0.045	22	14	3.3	38	91335
IRLU2705	55	0.04	24	0	15	46	91317
IRLU2905	55	0.027	36	23	1.8	69	91334
IRLU3103	30	0.019	46	29	1.8	69	91333
P-Channel							
IRFU9014	-60	0.5	-5.1	-3.2	5	25	90654
IRFU9024	-60	0.28	-8.8	-5.6	3	42	90655
IRFU9110	-100	1.2	-3.1	-2	5	25	90519
IRFU9120	-100	0.6	-5.6	-3.6	3	42	90520
IRFU9210	-200	3	-1.9	-1.2	5	25	90521
IRFU9220	-200	1.5	-3.6	-2.3	3	42	90522

HEXFET® Power MOSFETs

Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_D Continuous Drain Current 100°C (A)	$R_{\theta C}$ Max Thermal Resistance (°C/W)	P_D Max. Power Dissipation @ $T_C = 25^\circ\text{C}$ (W)	Fax-on- Demand
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Discrete

HEXDIP (HD-1)

N-Channel

IRFD014	60	0.2	1.7	1.2	120	1.3	90700
IRFD024	60	0.1	2.5	1.8	120	1.3	90699
IRFD110	100	0.54	1	0.71	120	1.3	90328
IRFD120	100	0.27	1.3	0.94	120	1.3	90385
IRFD210	200	1.5	0.6	0.38	120	1.3	90386
IRFD214	250	2	0.57	0.32	120	1.3	91271
IRFD220	200	0.8	0.8	0.5	120	1.3	90417
IRFD224	250	1.1	0.76	0.43	120	1.3	91272
IRFD310	400	3.6	0.42	0.23	120	1.3	91225
IRFD320	400	1.8	0.6	0.33	120	1.3	91226
IRFD420	500	3	0.46	0.26	120	1.3	91227
IRFDC20	600	4.4	0.32	0.21	120	1.3	91228

N-Channel

Logic Level

IRLD014	60	0.2	1.7	1.2	120	1.3	90628
IRLD024	60	0.1	2.5	1.8	120	1.3	90629
IRLD110	100	0.54	1	0.7	120	1.3	90635
IRLD120	100	0.27	1.3	0.94	120	1.3	90634

P-Channel

IRFD9014	-60	0.5	-1.1	-0.8	120	1.3	90696
IRFD9024	-60	0.28	-1.6	-1.1	120	1.3	90698

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Discrete

HEXDIP (HD-1)

IRFD9110	-100	1.2	-0.7	-0.49	120	1.3	90389
IRFD9120	-100	0.6	-1	-0.7	120	1.3	90331
IRFD9210	-200	3	-0.4	-0.25	120	1.3	90387
IRFD9220	-200	1.5	-0.56	-0.36	120	1.3	90439

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Surface Mount

D²Pak

N-Channel		<i>FETKY (Co-packaged HEXFET Power MOSFET and Schottky Diode)</i>					
IRL3103D1S	30	0.014	54	34	1.8	3.1	91558
N-Channel							
IRF1010NS	55	0.012	72	51	1.2	3.8	91372
IRF1310NS	100	0.036	36	25	1.3	120	91514
IRF3205S	55	0.008	98	69	1	150	91304
IRF3415S	150	0.042	37	26	1	150	91509
IRF3710S	100	0.028	46	33	1	150	91310
IRF510S	100	0.54	5.6	4	3.5	43	90895
IRF520NS	100	0.2	9.5	6.7	3.2	47	91340
IRF530NS	100	0.11	15	11	2.4	63	91352
IRF530S	100	0.16	14	10	1.7	88	90897
IRF540NS	100	0.052	27	19	1.6	110	91342
IRF540S	100	0.077	28	20	1	150	90898
IRF610S	200	1.5	3.3	2.1	3.5	36	90899
IRF614S	250	2	2.7	1.7	3.5	36	91003
IRF620S	200	0.8	5.2	3.3	2.5	50	90900
IRF624S	250	1.1	4.4	2.8	2.5	50	91004
IRF630S	200	0.4	9	5.7	1.7	74	90901
IRF634S	250	0.45	8.1	5.1	1.7	74	91005
IRF640S	200	0.18	18	11	1	125	90902

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Surface Mount

D²Pak

IRF644S	250	0.28	14	8.5	1	125	91006
IRF710S	400	3.6	2	1.2	3.5	36	91007
IRF720S	400	1.8	3.3	2.1	2.5	50	91008
IRF730S	400	1	5.5	3.3	1.7	74	91009
IRF740S	400	0.55	10	6.3	1	125	91010
IRF820S	500	3	2.5	1.6	2.5	50	91011
IRF830S	500	1.5	4.5	2.9	1.7	74	91012
IRF840S	500	0.85	8	5.1	1	125	91013
IRFZ14S	60	0.2	10	7.2	3.5	43	90890
IRFZ24NS	55	0.07	17	12	3.3	45	91355
IRFZ24S	60	0.1	17	12	2.5	60	90891
IRFZ34NS	55	0.04	26	18	2.7	56	91311
IRFZ34S	60	0.05	30	21	1.7	88	90892
IRFZ44N	55	0.024	41	29	1.8	83	91303
IRFZ44NS	60	0.028	50	36	1	150	91315
IRFZ44S	60	0.028	50	36	1	150	90893
IRFZ46NS	55	0.02	46	33	1.7	88	91305
IRFZ46S	50	0.024	50	38	1	150	90922
IRFZ48NS	60	0.016	53	37	1.6	3.8	91408
IRFZ48S	60	0.018	50	50	0.8	190	90894
IRL2505S	55	0.008	90	64	1	2.1	91326
IRL2703S	30	0.04	24	17	3.3	130	91360

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International
 Rectifier

Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_D Continuous Drain Current 100°C (A)	$R_{\theta C}$ Max Thermal Resistance (°C/W)	P_D Max. Power Dissipation @ $T_C = 25^\circ\text{C}$ (W)	Fax-on- Demand
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Surface Mount

D²Pak

IRL530NS	100	0.1	15	11	2.4	63	91349
IRL620S	200	0.8	5.2	3.3	2.5	50	91218
N-Channel		<i>Logic Level</i>					
IRL2203NS	30	0.007	100	71	1.2	130	91367
IRL3103S	30	0.014	56	40	1.8	83	91338
IRL3303S	30	0.026	34	24	2.7	56	91323
IRL3705NS	55	0.01	77	54	1.2	3.8	91502
IRL3803S	30	0.006	120	83	1	150	91319
IRL510S	100	0.54	5.6	4	3.5	43	90907
IRL520S	100	0.27	9.2	6.5	2.5	60	90896
IRL530S	100	0.16	15	10	1.7	88	90909
IRLZ14S	60	0.2	10	7.2	3.5	43	90903
IRLZ24NS	55	0.06	18	13	3.3	45	91358
IRLZ24S	60	0.1	17	12	2.5	60	90904
IRLZ34NS	55	0.035	27	19	2.7	56	91308
IRLZ34S	60	0.05	30	21	1.7	88	90905
IRLZ44NS	55	0.022	41	29	1.8	83	91347
IRLZ44S	60	0.028	50	36	1	150	90906
P-Channel							
IRF4905S	-55	0.02	-64	-45	1	150	91478
IRF5210S	-100	0.06	-35	-25	1	150	91405

HEXFET® Power MOSFETs

International
IR Rectifier

Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_D Continuous Drain Current 100°C (A)	$R_{\theta C}$ Max Thermal Resistance (°C/W)	P_D Max. Power Dissipation @ $T_C = 25^\circ\text{C}$ (W)	Fax-on- Demand
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Surface Mount

D²Pak

IRF9510S	-100	1.2	-4	-2.8	3.5	43	90914
IRF9520S	-100	0.6	-6.8	-4.8	2.5	60	90915
IRF9530S	-100	0.3	-12	-8.2	1.7	88	90916
IRF9540S	-100	0.2	-19	-13	1	150	90917
IRF9610S	-200	3	-1.8	-1	6.4	20	90918
IRF9620S	-200	1.5	-2.5	-2	3.1	40	90919
IRF9630S	-200	0.8	-6.5	-4	1.7	74	90920
IRF9640S	-200	0.5	-11	-6.8	1	125	90921
IRF9Z14S	-60	0.5	-6.7	-4.7	3.5	43	90911

HEXFET® Power MOSFETs

International
 Rectifier

Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_{DQ} Total Drain Current 0 (nC)	$R_{\theta C}$ Max Thermal Resistance (°C/W)	P_D Max. Power Dissipation @ $T_C = 25^\circ\text{C}$ (W)	Qg Total Gate Charge (nC)	Fax-on- Demand
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Discrete

TO-220AB

N-Channel	<i>Low Charge</i>							
IRF737LC	300	0.75	6.1		1.7	74	3.9	91314
IRF740LC	400	0.55	10		1	125	39	91068
IRF840LC	500	0.85	8		1	125	39	91069
IRFBC40LC	600	1.2	6.2		1	125	39	91070

HEXFET® Power MOSFETs

Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_D Continuous Drain Current 100°C (A)	$R_{\theta C}$ Max Thermal Resistance (°C/W)	P_D Max. Power Dissipation @ $T_C = 25^\circ\text{C}$ (W)	Fax-on- Demand
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Discrete

TO-220AB

N-Channel		<i>FETKY (Co-packaged HEXFET Power MOSFET and Schottky Diode)</i>					
IRL3103D1	30	0.014	54	34	1.8	2	91608
N-Channel							
IRF1010N	55	0.012	72	51	1.2	130	91278
IRF1310N	100	0.036	36	25	1.3	120	91611
IRF3205	55	0.008	98	69	1	150	91279
IRF3415	150	0.042	37	26	1	150	91477
IRF3710	100	0.028	46	33	1	150	91309
IRF510	100	0.54	5.6	4	3.5	43	90325
IRF520N	100	0.2	9.5	6.7	9.5	47	91339
IRF530N	100	0.11	15	11	2.4	60	91351
IRF540N	100	0.052	27	19	1.6	94	91341
IRF610	200	1.5	3.3	2.1	3.5	36	90326
IRF614	250	2	2.7	1.7	3.5	36	90475
IRF620	200	0.8	5.2	3.3	2.5	50	90317
IRF624	250	1.1	4.4	2.8	2.5	50	90472
IRF630	200	0.4	9	5.7	1.7	74	90309
IRF634	250	0.45	8.1	5.1	1.7	74	90476
IRF640	200	0.18	18	11	1	125	90374
IRF644	250	0.28	14	8.5	1	125	90527
IRF710	400	3.6	2	1.2	3.5	36	90327

HEXFET® Power MOSFETs

Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_D Continuous Drain Current 100°C (A)	$R_{\theta C}$ Max Thermal Resistance (°C/W)	P_D Max. Power Dissipation @ $T_C = 25^\circ\text{C}$ (W)	Fax-on- Demand
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Discrete

TO-220AB

IRF720	400	1.8	3.3	2.1	2.5	50	90315
IRF730	400	1	5.5	3.3	1.7	74	90308
IRF734	450	1.2	4.9	3.1	1.7	74	90999
IRF740	400	0.55	10	6.3	1	125	90375
IRF744	450	0.63	8.8	5.6	1	125	91000
IRF820	500	3	2.5	1.6	2.5	50	90324
IRF830	500	1.5	4.5	2.9	1.7	74	90311
IRF840	500	0.85	8	5.1	1	125	90376
IRFBC20	600	4.4	2.2	1.4	2.5	50	90623
IRFBC30	600	2.2	3.6	2.3	1.7	74	90482
IRFBC40	600	1.2	6.2	3.9	1	125	90506
IRFBE20	800	6.5	1.8	1.2	2.3	54	90610
IRFBE30	800	3	4.1	2.6	2	125	90613
IRFBF20	900	8	1.7	1.1	2.3	54	90607
IRFBF30	900	3.7	3.6	2.3	1	125	90616
IRFBG20	1000	11	1.4	0.86	2.3	54	90604
IRFBG30	1000	5	3.1	2	1	125	90620
IRFZ14	60	0.2	10	7.2	3.5	43	90507
IRFZ24N	55	0.07	17	12	3.3	45	91354
IRFZ34N	55	0.04	26	18	2.7	56	91276
IRFZ46N	55	0.02	46	33	1.7	88	91277
IRFZ48N	55	0.016	53	37	1.6	94	91406

HEXFET® Power MOSFETs

Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_D Continuous Drain Current 100°C (A)	$R_{\theta C}$ Max Thermal Resistance (°C/W)	P_D Max. Power Dissipation @ $T_C = 25^\circ\text{C}$ (W)	Fax-on- Demand
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Discrete

TO-220AB

N-Channel	<i>Logic Level</i>						
IRL2203N	30	0.007	100	71	1.2	130	91366
IRL3103	30	0.014	56	40	1.8	83	91337
IRL3303	30	0.026	34	24	2.7	56	91322
IRL3705N	55	0.01	77	54	1.2	130	91370
IRL3803	30	0.006	120	83	1	150	91301
IRL520N	100	3.2	10	7.1	3.2	47	91494
IRL530N	100	0.1	15	11	2.4	63	91348
IRL540N	100	0.044	30	21	1.6	94	91495
IRL640	200	0.18	17	11	1	125	91089
IRLI2203N	30	0.007	61	43	3.2	47	91378
IRLZ14	60	0.2	10	7.2	3.5	43	90556
IRLZ24N	55	0.06	18	13	3.3	45	91357
IRLZ34N	55	0.035	27	19	2.7	56	91307
IRLZ44N	55	0.022	41	29	1.8	83	91346
P-Channel							
IRF4905	-55	0.02	-64	-45	1	150	91280
IRF9510	-100	1.2	-4	-2.8	3.5	43	90390
IRF9520	-100	0.6	-6.8	-4.8	2.5	60	90319
IRF9530N	-100	0.2	-13	-9.2	2	75	91482
IRF9540N	-100	0.117	-19	-13	1.6	94	91437

HEXFET® Power MOSFETs

International
IOR Rectifier

Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_D Continuous Drain Current 100°C (A)	$R_{\theta C}$ Max Thermal Resistance (°C/W)	P_D Max. Power Dissipation @ $T_C = 25^\circ\text{C}$ (W)	Fax-on- Demand
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Discrete

TO-220AB

IRF9610	-200	3	-1.8	-1	6.4	20	90350
IRF9620	-200	1.5	-2.5	-2	3.1	40	90351
IRF9630	-200	0.8	-6.5	-4	1.7	74	90352
IRF9640	-200	0.5	-11	-6.8	1	125	90422
IRF9Z14	-60	0.5	-6.7	-4.7	3.5	43	90736
IRF9Z24N	-55	0.175	-12	-8.5	3.3	45	91484
IRF9Z34N	-55	0.1	-17	-12	2.7	56	92001

HEXFET® Power MOSFETs

International
 Rectifier

Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_{DQ} Total Drain Current 0 (nC)	$R_{\theta C}$ Max Thermal Resistance (°C/W)	P_D Max. Power Dissipation @ $T_C = 25^\circ\text{C}$ (W)	Q_g Total Gate Charge (nC)	Fax-on- Demand
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Fully Isolated

TO-220 FullPak

N-Channel

Low Charge

IRFI740GLC	400	0.55	6		3.1	40	39	91209
IRFI840GLC	500	0.85	4.8		3.1	40	39	91208
IRFIBC40GLC	600	1.2	4		3.1	40	39	91211

HEXFET® Power MOSFETs

Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_D Continuous Drain Current 100°C (A)	$R_{\theta C}$ Max Thermal Resistance (°C/W)	P_D Max. Power Dissipation @ $T_C = 25^\circ\text{C}$ (W)	Fax-on- Demand
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Fully Isolated

TO-220 Full-Pak

N-Channel

IRFI1010N	55	0.012	44	31	3.2	47	91373
IRFI1310N	100	0.036	22	16	3.3	45	91611
IRFI3205	55	0.008	56	40	3.1	48	91374
IRFI510G	100	0.54	4.5	3.2	5.5	27	90829
IRFI520N	100	0.2	7.2	5.1	5.5	27	91362
IRFI530N	100	0.11	11	7.8	4.5	33	91353
IRFI540N	100	0.052	18	13	3.6	42	91361
IRFI614G	250	2	2.1	1.3	5.5	23	90831
IRFI620G	200	0.8	4.1	2.6	4.1	30	90832
IRFI624G	250	1.1	3.4	2.2	4.1	30	90833
IRFI630G	200	0.4	5.9	3.7	3.6	32	90652
IRFI634G	250	0.45	5.6	3.5	3.6	32	90738
IRFI640G	200	0.18	9.8	6.2	3.1	40	90649
IRFI644G	250	0.28	7.9	5	3.1	40	90739
IRFI720G	400	1.8	2.6	1.7	4.1	30	90834
IRFI730G	400	1	3.7	2.3	3.6	32	90650
IRFI734G	450	1.2	3.4	2.1	3.6	35	91001
IRFI740G	400	0.55	5.4	3.4	3.1	40	90651
IRFI744G	450	0.63	4.9	3.1	3.1	40	91002
IRFI820G	500	3	2.1	1.3	4.1	30	90641

HEXFET® Power MOSFETs

Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_D Continuous Drain Current 100°C (A)	$R_{\theta C}$ Max Thermal Resistance (°C/W)	P_D Max. Power Dissipation @ $T_C = 25^\circ\text{C}$ (W)	Fax-on- Demand
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Fully Isolated

TO-220 FullPak

IRFI830G	500	1.5	3.1	2	3.6	32	90646
IRFI840G	500	0.85	4.6	2.9	3.1	40	90642
IRFIBC20G	600	4.4	1.7	1.1	4.1	30	90850
IRFIBC30G	600	2.2	2.5	1.6	3.6	35	90851
IRFIBC40G	600	1.2	3.5	2.2	3.1	40	90852
IRFIBE20G	800	6.5	1.4	0.86	4.1	30	90853
IRFIBE30G	800	3	2.1	1.4	3.6	35	90854
IRFIBF20G	900	8	1.2	0.79	4.1	30	90855
IRFIBF30G	900	3.7	1.9	1.2	3.6	35	90856
IRFIZ14G	60	0.2	8	5.7	5.5	27	90859
IRFIZ24N	55	0.07	13	9.2	5.8	26	91501
IRFIZ34N	55	0.04	19	13	4.8	31	91489
IRFIZ44N	55	0.024	28	20	0.024	38	91403
IRFIZ46N	55	0.02	31	22	3.8	40	91306
IRFIZ48N	55	0.016	36	25	3.6	42	91407
N-Channel	<i>Logic Level</i>						
IRLI3705N	55	0.01	47	33	3.2	47	91369
IRLI3803	30	0.006	67	47	3.1	48	91320
IRLI520N	100	0.18	7.7	5.4	5.5	27	91496
IRLI530G	100	0.16	9.7	6.9	3.6	42	90844
IRLI540N	100	0.044	20	14	3.6	42	91497

HEXFET® Power MOSFETs

Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_D Continuous Drain Current 100°C (A)	$R_{\theta C}$ Max Thermal Resistance (°C/W)	P_D Max. Power Dissipation @ $T_C = 25^\circ\text{C}$ (W)	Fax-on- Demand
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Fully Isolated

TO-220 FullPak

IRLI620G	200	0.8	4.1	2.6	4.1	30	91235
IRLI630G	200	0.4	5.9	3.7	3.6	32	91236
IRLI640G	200	0.18	9.8	6.2	3.1	40	91237
IRLIZ14G	60	0.2	8	5.7	5.5	27	90846
IRLIZ24G	60	0.1	14	10	4.1	37	90847
IRLIZ24N	55	0.06	14	9.9	5.8	26	91344
IRLIZ34N	55	0.035	20	14	4.8	31	91329
IRLIZ44N	55	0.022	28	20	4	38	91498
P-Channel							
IRFI9540G	-100	0.117	-13	-9.2	3.6	42	90837
IRFI9540N	-100	0.117	-13	-9.2	3.6	42	91487
IRFI9634G	-250	1	-4.1	-2.6	3.6	35	91488
P-Channel <i>Logic Level</i>							
IRFI9520G	-100	0.6	-5.2	-3.6	4.1	37	90835
IRFI9530G	-100	0.03	-7.7	-5.4	3.6	38	90836
IRFI9620G	-200	1.5	-3	-1.9	4.1	30	90874
IRFI9630G	-200	0.8	-4.3	-2.7	3.6	40	90838
IRFI9640G	-200	0.5	-6.1	-3.9	3.1	40	90839
IRFI9Z14G	-60	0.5	-5.3	-3.8	5.5	27	90840
IRFI9Z24G	-60	0.285	-8.5	-6	4.1	37	90841
IRFI9Z34G	-60	0.14	-12	8.5	3.6	38	90842

HEXFET® Power MOSFETs

International
IR Rectifier

Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_D Continuous Drain Current 100°C (A)	$R_{\theta C}$ Max Thermal Resistance (°C/W)	P_D Max. Power Dissipation @ $T_C = 25^\circ\text{C}$ (W)	Nominal Sense Number	Fax-on- Demand
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HEXSENSE

TO-220 Hexsense

N-Channel

IRC530	100	0.16	14	10	1.7	88	1540	90454
IRC540	100	0.077	28	20	1	150	2810	90592
IRC630	200	0.4	9	5.7	1.7	74	1570	90565
IRC634	250	0.45	8.1	5.1	1.7	74	1580	90566
IRC640	200	0.18	18	11	1	125	2880	90568
IRC644	250	0.28	14	8.5	1	125	2900	90569
IRC730	400	1	5.5	3.5	1	74	1600	90567
IRC740	400	0.55	10	6.3	1	125	2940	90570
IRC830	500	1.5	4.5	3	1.7	74	1600	90455
IRC840	500	0.85	8	5.1	1	125	2970	90593
IRCZ24	60	0.1	17	12	2.5	60	820	90615
IRCZ34	60	0.05	30	21	1.7	88	1480	90590
IRCZ44	60	0.028	50	37	1	150	2720	90529

HEXFET® Power MOSFETs

International
 Rectifier

Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_D Drain Current	$R_{\theta C}$ Max Thermal Resistance (°C/W)	P_D Max. Power Dissipation @ $T_C = 25^\circ\text{C}$ (W)	Qg Total Gate Charge (nC)	Fax-on- Demand
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Discrete

TO-247AC

N-Channel

Low Charge

IRFP350LC	400	0.3	18		0.65	190	70	91229
IRFP360LC	400	0.2	23		0.45	280	98	91230
IRFP450LC	500	0.4	16		0.65	190	70	91231
IRFP460LC	500	0.27	20		0.45	280	98	91232
IRFPC50LC	600	0.6	13		0.65	190	70	91233
IRFPC60LC	600	0.4	16		0.45	280	98	91234

HEXFET® Power MOSFETs

Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_D Continuous Drain Current 100°C (A)	$R_{\theta C}$ Max Thermal Resistance (°C/W)	P_D Max. Power Dissipation @ $T_C = 25^\circ\text{C}$ (W)	Fax-on- Demand
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Discrete

TO-247AC

N-Channel

IRFP044N	55	0.02	49	35	1.5	100	91410
IRFP048N	55	0.016	62	44	1.2	130	91409
IRFP054N	55	0.012	72	51	1.2	130	91382
IRFP064N	55	0.008	98	69	1	150	91383
IRFP140N	100	0.052	27	19	1.6	94	91343
IRFP150N	100	0.036	39	28	1.1	140	91503
IRFP240	200	0.18	20	12	0.83	150	90444
IRFP244	250	0.28	15	9.7	0.83	150	90588
IRFP250	200	0.085	30	19	0.65	190	90443
IRFP254	250	0.14	23	15	0.65	190	90540
IRFP260	200	0.055	46	29	0.45	280	90755
IRFP264	250	0.075	38	24	0.45	280	90756
IRFP340	400	0.55	11	6.9	0.83	150	90456
IRFP344	450	0.63	9.5	6	0.83	150	90998
IRFP350	400	0.3	16	10	0.65	190	90445
IRFP354	450	0.35	14	9.1	0.65	190	90995
IRFP360	400	0.2	23	14	0.45	280	90586
IRFP3710	100	0.028	51	36	0.83	180	91490
IRFP440	500	0.85	8.8	5.6	0.83	150	90457
IRFP448	500	0.6	11	6.6	0.7	180	90595

HEXFET® Power MOSFETs

Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_D Continuous Drain Current 100°C (A)	$R_{\theta C}$ Max Thermal Resistance (°C/W)	P_D Max. Power Dissipation @ $T_C = 25^\circ\text{C}$ (W)	Fax-on- Demand
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Discrete

TO-247AC

IRFP450	500	0.4	14	8.7	0.65	190	90458
IRFP460	500	0.27	20	13	0.45	280	90512
IRFPC30	600	2.2	4.3	2.7	1.2	100	90596
IRFPC40	600	1.2	6.8	4.3	0.83	150	90511
IRFPC48	600	0.82	8.9	5.6	0.73	170	90996
IRFPC50	600	0.6	11	7	0.65	180	90656
IRFPC60	600	0.4	16	10	0.45	280	90870
IRFPE30	800	3	4.1	2.6	1	125	90612
IRFPE40	800	2	5.4	3.4	0.83	150	90578
IRFPE50	800	1.2	7.8	4.9	0.65	190	90573
IRFPF30	900	3.7	3.6	2.3	1	125	90618
IRFPF40	900	2.5	4.7	2.9	0.83	150	90580
IRFPF50	900	1.6	6.7	4.2	0.65	190	90542
IRFPG30	1000	5	3.1	2	1	125	90621
IRFPG40	1000	3.5	4.3	2.7	0.83	150	90576
IRFPG50	1000	2	6.1	3.9	0.65	190	90543
P-Channel							
IRFP9140	-100	0.2	-21	-15	0.83	180	90480
IRFP9240	-200	0.5	-12	-7.5	0.83	150	90481

HEXFET® Power MOSFETs

Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_{DM} Pulse Drain Current 100°C (A)	$R_{\theta C}$ Max Thermal Resistance (°C/W)	P_D Max. Power Dissipation (W)	Fax-on- Demand
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HEX-Pak Module

TO-240AA

N-Channel	<i>Parallel Chip</i>					
IRFK4H054	60	0.005	150	960	0.25	500
IRFK4H150	100	0.014	145	580	0.25	500
IRFK4H250	200	0.021	108	432	0.25	500
IRFK4H350	400	0.075	50	200	0.25	500
IRFK4H450	500	0.1	44	176	0.25	500
IRFK4HC50	600	0.175	35	140	0.25	500
IRFK4HE50	800	0.3	26	104	0.25	500
IRFK4J054	60	0.005	150	960	0.25	500
IRFK4J150	100	0.014	145	580	0.25	500
IRFK4J250	200	0.021	108	432	0.25	500
IRFK4J350	400	0.075	50	200	0.25	500
IRFK4J450	500	0.1	44	176	0.25	500
IRFK4JC50	600	0.175	35	140	0.25	500
IRFK4JE50	800	0.3	26	104	0.25	500
IRFK6H054	60	0.003	350	1400	0.2	625
IRFK6H150	100	0.01	150	720	0.2	625
IRFK6H250	200	0.015	140	560	0.2	625
IRFK6H350	400	0.05	75	300	0.2	625
IRFK6H450	500	0.067	66	264	0.2	625
IRFK6HC50	600	0.1	48	192	0.2	625

HEXFET® Power MOSFETs

International
IOR Rectifier

Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_{DM} Pulse Drain Current 100°C (A)	$R_{\theta C}$ Max Thermal Resistance (°C/W)	P_D Max. Power Dissipation (W)	Fax-on- Demand
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HEX-Pak Module

TO-240AA

IRFK6J054	60	0.003	350	1400	0.2	625	
IRFK6J150	100	0.01	150	720	0.2	625	
IRFK6J250	200	0.015	140	560	0.2	625	
IRFK6J350	400	0.05	75	300	0.2	625	
IRFK6J450	500	0.067	66	264	0.2	625	
IRFK6JC50	600	0.1	48	192	0.2	625	

HEXFET® Power MOSFETs

International
 Rectifier

Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_{DM} Pulse Drain Current 100°C (A)	$R_{\theta C}$ Max Thermal Resistance (°C/W)	P_D Max. Power Dissipation (W)	Fax-on- Demand
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HEX-Pak Module

TO-240AA

N-Channel	<i>Half Bridge</i>					
IRFK2D054	60	0.01	120	480	0.25	500
IRFK2D150	100	0.028	72	288	0.25	500
IRFK2D250	200	0.043	54	216	0.25	500
IRFK2D350	400	0.15	25	100	0.25	500
IRFK2D450	500	0.2	22	88	0.25	500
IRFK2DC50	600	0.35	18	72	0.25	500
IRFK2DE50	800	0.6	12	48	0.25	500
IRFK2F054	60	0.01	120	480	0.25	500
IRFK2F150	100	0.028	72	288	0.25	500
IRFK2F250	200	0.043	54	216	0.25	500
IRFK2F350	400	0.15	25	100	0.25	500
IRFK2F450	500	0.2	22	88	0.25	500
IRFK2FC50	600	0.35	18	72	0.25	500
IRFK2FE50	800	0.6	12	48	0.25	500
IRFK3D150	100	0.02	125	435	0.2	625
IRFK3D250	200	0.03	70	280	0.2	625
IRFK3D350	400	0.1	37	148	0.2	625
IRFK3D450	500	0.135	33	132	0.2	625
IRFK3DC50	600	0.23	24	96	0.2	625
IRFK3F150	100	0.02	125	435	0.2	625

HEXFET® Power MOSFETs

International
IOR Rectifier

Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_{DM} Pulse Drain Current 100°C (A)	$R_{\theta C}$ Max Thermal Resistance (°C/W)	P_D Max. Power Dissipation (W)	Fax-on- Demand
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HEX-Pak Module

TO-240AA

IRFK3F250	200	0.03	70	280	0.2	625	
IRFK3F350	400	0.1	37	148	0.2	625	
IRFK3F450	500	0.135	33	132	0.2	625	
IRFK3FC50	600	0.23	24	96	0.2	625	